



IFN5432, IFN5433, IFN5434 N-Channel JFET

Features

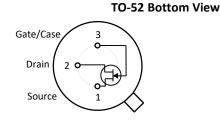
- InterFET <u>N0903L Geometry</u>
- Low Noise: 0.7 nV/VHz Typical
- High Gain: 200mS Typical
- Low Rds(on): 5 Ohms Max (IFN5432)
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

Applications

- Low On Resistance Switches
- Choppers

Description

The -25V InterFET IFN5432, IFN5433, and IFN5434 are targeted for Low resistance switches and choppers. The TO-52 package is hermetically sealed and suitable for military applications.





Product Summary

Parameters		IFN5432 Min	IFN5433 Min	IFN5434 Min	Unit	
BV _{GSS}	Gate to Source Breakdown Voltage	-25	-25	-25	V	
I _{DSS}	Drain to Source Saturation Current	150	100	30	mA	
V _{GS(off)}	Gate to Source Cutoff Voltage	-4	-3	-1	V	

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFN5432; IFN5433; IFN5434	Through-Hole	TO-52	Bulk
IFN5432COT; IFN5433COT			
IFN5343COT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
IFN5432CFT; IFN5433CFT			
IFN5434CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.







Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit	
VRGS	Reverse Gate Source and Gate Drain Voltage	-25	V	
I_{FG}	Continuous Forward Gate Current	100	mA	
PD	Continuous Device Power Dissipation	300	mW	
Р	Power Derating	2.4	mW/°C	
Τı	Operating Junction Temperature	-55 to 125	°C	
T _{STG}	Storage Temperature	-65 to 150	°C	

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN5432		IFN5433		IFN5434		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
V(BR)GSS	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1µA	-25		-25		-25		v
I _{GSS}	Gate to Source Reverse Current	V _{DS} = -15V, V _{GS} = 0V, T _A = 25°C V _{DS} = -15V, V _{GS} = 0V, T _A = 150°C		-200 -200		-200 -200		-200 -200	pA nA
Vgs(off)	Gate to Source Cutoff Voltage	V _{DS} = 5V, I _D = 3nA	-4	-10	-3	-9	-1	-4	v
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V, V_{DS} = 15V$ (Pulsed)	150		100		30		mA
I _{D(OFF)}	Drain Cutoff Current	V _{DS} = 5V, V _{GS} = -10V, T _A = 25°C V _{DS} = 5V, V _{GS} = -10V, T _A = 150°C		200 200		200 200		200 200	pA nA
V _{DS(ON)}	Drain to Source ON Voltage	$V_{GS} = 0V, I_D = 10mA$		50		70		100	mV
Rds(on)	Static Drain to Source ON Resistance	V _{GS} = 0V, I _D = 10mA	2	5		7		10	Ω

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

		IFN5432		5432	IFN5433		IFN5434		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
R _{DS(ON)}	Drain to Source ON Resistance	V_{GS} = 0V, I_D = 0A, f = 1kHz		5		7		10	Ω
Ciss	Input Capacitance	$V_{DS} = 0V, V_{GS} = -10V, f = 1MHz$		60		60		60	рF
Crss	Reverse Transfer Capacitance	V _{DS} = 0V, V _{GS} = -10V, f = 1MHz		20		20		20	pF
t _{d(ON)}	Turn-On Delay Time	$V_{DD} = 1.5V, V_{GS(ON)} = 0V,$ $V_{GS(OFF)} = -12V, I_{D(ON)} = 10mA$		4		4		4	ns
tr	Rise Time			1		1		1	ns
t _{d(OFF)}	Turn-Off Delay Time			6		6		6	ns
t _f	Fall Time			30		30		30	ns

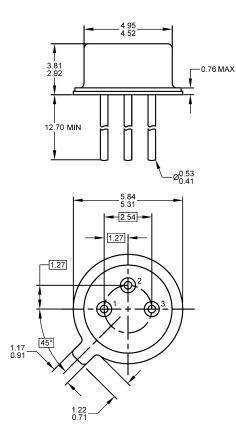




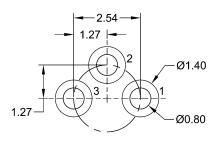
IFN5432-3-4

TO-52 Mechanical and Layout Data

Package Outline Data



Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.26 grams
- 3. Bulk product is shipped in standard ESD shipping material
- 4. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.